

Product data sheet

### 1. General description

NPN low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

PNP complement: PBSS5260QA.

### 2. Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- High energy efficiency due to less heat generation
- Reduced Printed-Circuit Board (PCB) area requirements
- Solderable side pads
- AEC-Q101 qualified

### 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 4. Quick reference data

| Table 1. Quick reference data |  |  |  |     |     |     |      |
|-------------------------------|--|--|--|-----|-----|-----|------|
| Symbol                        | Parameter                                  | Conditions   |  | Min | Тур | Max | Unit |
| V <sub>CEO</sub>              | collector-emitter<br>voltage               | open base  |  | -   | -   | 60  | V    |
| I <sub>C</sub>                | collector current                          |  |  | -   | -   | 2   | А    |
| I <sub>CM</sub>               | peak collector current                     | single pulse; t <sub>p</sub> ≤ 1 ms  |  | -   | -   | 3   | А    |
| R <sub>CEsat</sub>            | collector-emitter<br>saturation resistance | $\begin{split} I_C = 1 \text{ A}; \ I_B = 0.1 \text{ A}; \ \text{pulsed}; \ t_p \leq 300 \ \mu\text{s}; \\ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^\circ\text{C} \end{split}$ |  | -   | 130 | 180 | mΩ   |

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### 5. Pinning information

| Table 2. | Pinning | information |   |                |
|----------|---------|-------------|---|----------------|
| Pin      | Symbol  | Description | Simplified outline                        | Graphic symbol |
| 1        | В       | base        |   | С              |
| 2        | E       | emitter     |   | в              |
| 3        | С       | collector   | 4 3                                       | <b>N</b>       |
| 4        | С       | collector   | Transparent top view DFN1010D-3 (SOT1215) | E<br>sym123    |

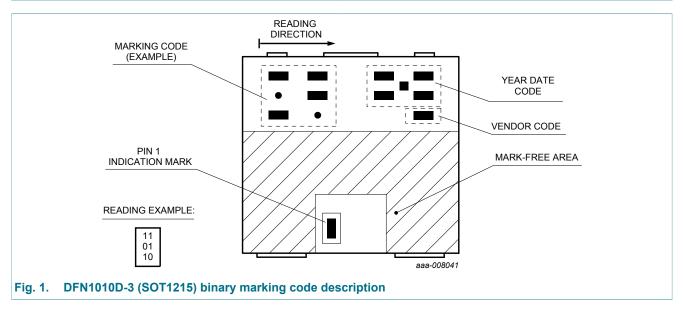
# 6. Ordering information

| Table 3. Ordering information |            |  |         |  |  |  |
|-------------------------------|------------|--|---------|--|--|--|
| Type number                   | Package    |  |         |  |  |  |
|                               | Name       | Description  | Version |  |  |  |
| PBSS4260QA                    | DFN1010D-3 | plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals | SOT1215 |  |  |  |

# 7. Marking

#### Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PBSS4260QA  | 11 11 00     |



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### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                 | Conditions                          |     | Min | Мах  | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|------|------|
| V <sub>CBO</sub> | collector-base voltage    | open emitter                        |     | -   | 60   | V    |
| V <sub>CEO</sub> | collector-emitter voltage | open base                           |     | -   | 60   | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                      |     | -   | 7    | V    |
| I <sub>C</sub>   | collector current         |                                     |     | -   | 2    | А    |
| I <sub>CM</sub>  | peak collector current    | single pulse; t <sub>p</sub> ≤ 1 ms |     | -   | 3    | А    |
| I <sub>B</sub>   | base current              |                                     |     | -   | 0.3  | А    |
| I <sub>BM</sub>  | peak base current         | single pulse; t <sub>p</sub> ≤ 1 ms |     | -   | 1    | А    |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 325  | mW   |
|                  |                           |                                     | [2] | -   | 600  | mW   |
|                  |                           |                                     | [3] | -   | 740  | mW   |
|                  |                           |                                     | [4] | -   | 540  | mW   |
|                  |                           |                                     | [5] | -   | 1000 | mW   |
| Tj               | junction temperature      |                                     |     | -   | 150  | °C   |
| T <sub>amb</sub> | ambient temperature       |                                     |     | -55 | 150  | °C   |
| T <sub>stg</sub> | storage temperature       |                                     |     | -65 | 150  | °C   |

[1] Device mounted on an FR4 PCB single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

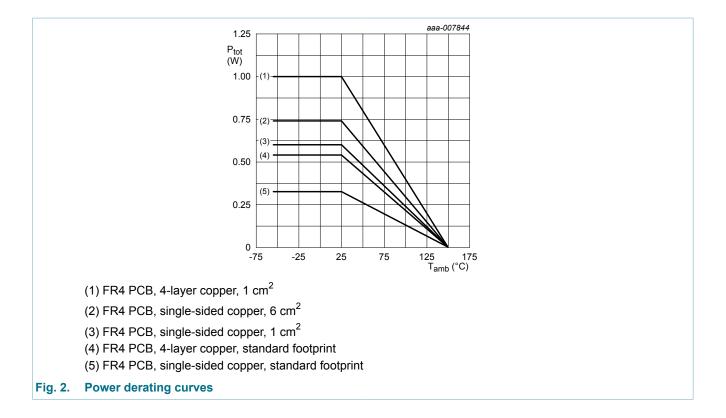
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

<sup>[5]</sup> Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

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### 9. Thermal characteristics

| Table 6.         Thermal characteristics |                             |             |     |     |     |     |      |  |
|--|-----------------------------|-------------|-----|-----|-----|-----|------|--|
| Symbol                                   | Parameter                   | Conditions  |     | Min | Тур | Max | Unit |  |
| frc                                      | thermal resistance          | in free air | [1] | -   | -   | 385 | K/W  |  |
|  | from junction to<br>ambient |             | [2] | -   | -   | 209 | K/W  |  |
|  | ampient                     |             | [3] | -   | -   | 169 | K/W  |  |
|  |                             |             | [4] | -   | -   | 232 | K/W  |  |
|  |                             |             | [5] | -   | -   | 125 | K/W  |  |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

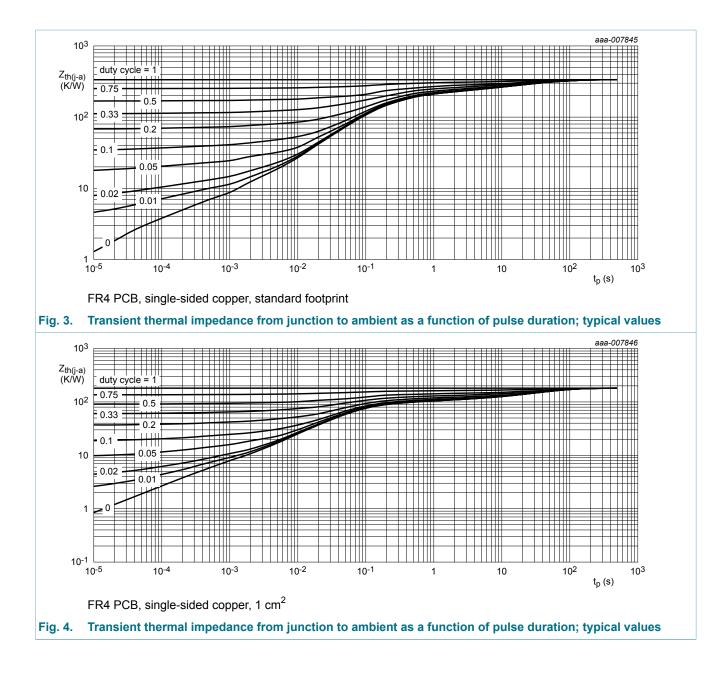
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

<sup>[5]</sup> Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

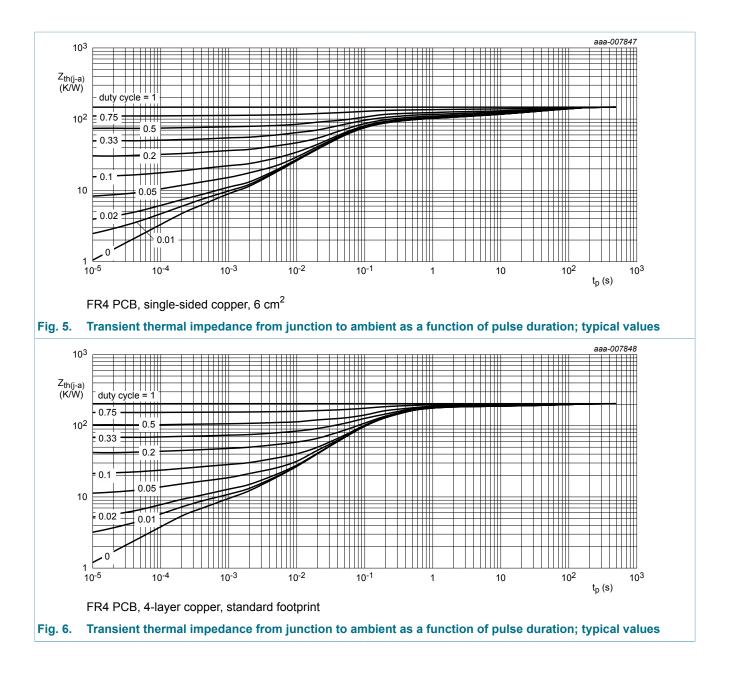


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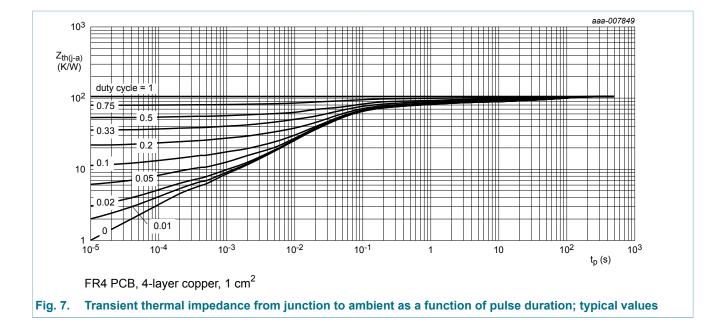


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### **10. Characteristics**

| Symbol             | Parameter                            | Conditions  | Min | Тур | Max | Unit |
|--------------------|--------------------------------------|---|-----|-----|-----|------|
| I <sub>CBO</sub>   | collector-base cut-off               | V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C  | -   | -   | 100 | nA   |
| cui                | current                              | V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C   | -   | -   | 50  | μA   |
| I <sub>CES</sub>   | collector-emitter cut-off current    | $V_{CE}$ = 48 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C  | -   | -   | 100 | nA   |
| I <sub>EBO</sub>   | emitter-base cut-off current         | $V_{EB}$ = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C  | -   | -   | 100 | nA   |
| h <sub>FE</sub>    | DC current gain                      | $V_{CE}$ = 2 V; I <sub>C</sub> = 100 mA; pulsed;<br>t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02 ; T <sub>amb</sub> = 25 °C   | 235 | 400 | -   |      |
|                    |                                      | $\begin{split} &V_{CE} \texttt{= 2 V; } I_{C} \texttt{= 500 mA; pulsed;} \\ &t_{p} \texttt{\le 300 \mu s; } \overline{o} \texttt{\le 0.02 ; } T_{amb} \texttt{= 25 °C} \end{split}$         | 150 | 240 | -   |      |
|                    |                                      | $\label{eq:Vce} \begin{split} V_{CE} &= 2 \; V; \; I_C = 1 \; A; \; \text{pulsed}; \; t_p \leq 300 \; \mu\text{s}; \\ \delta &\leq 0.02 \; ; \; T_{amb} = 25 \; ^\circ\text{C} \end{split}$ | 85  | 125 | -   |      |
|                    |                                      | $V_{CE} = 2 \text{ V; } I_C = 2 \text{ A; pulsed; } t_p \le 300  \mu\text{s;}$<br>$\delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$  | 40  | 65  | -   |      |
| V <sub>CEsat</sub> | collector-emitter saturation voltage | I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA; pulsed;<br>t <sub>p</sub> ≤ 300 μs; $\delta$ ≤ 0.02 ; T <sub>amb</sub> = 25 °C   | -   | 75  | 100 | mV   |
|                    |                                      | $I_{C}$ = 1 A; $I_{B}$ = 50 mA; pulsed;<br>$t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C  | -   | 145 | 190 | mV   |
|                    |                                      | $I_{C}$ = 1 A; $I_{B}$ = 100 mA; pulsed;<br>$t_{p} \le 300 \ \mu$ s; $\overline{\delta} \le 0.02$ ; $T_{amb}$ = 25 °C   | -   | 130 | 180 | mV   |

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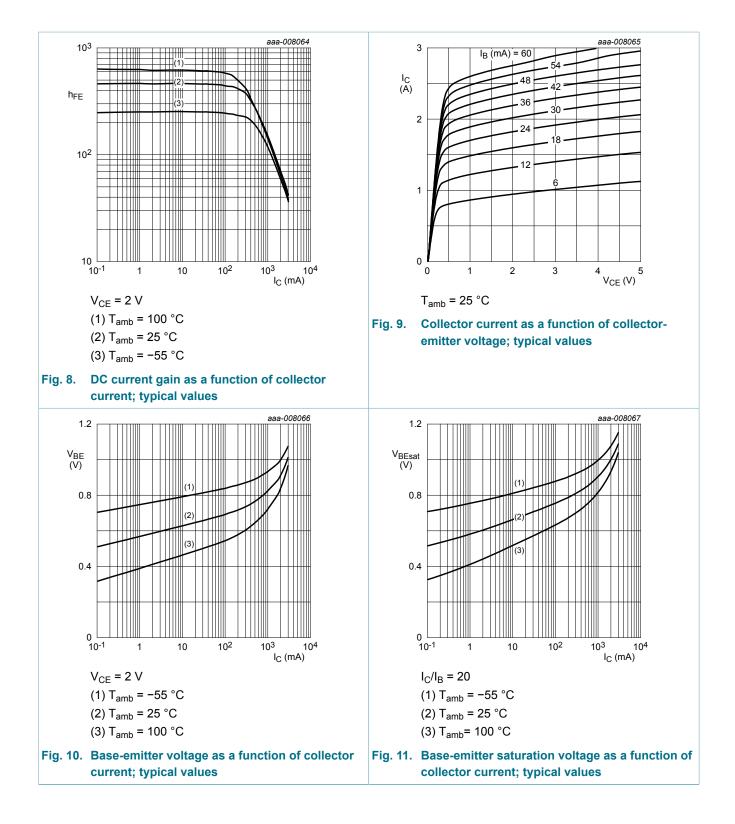
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### 60 V, 2 A NPN low VCEsat (BISS) transistor

| Symbol             | Parameter                               | Conditions  | Min | Тур  | Max  | Unit |
|--------------------|---|---|-----|------|------|------|
|                    |   | $I_{C}$ = 2 A; $I_{B}$ = 100 mA; pulsed;<br>$t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C   | -   | 275  | 370  | mV   |
|                    |   | $I_C$ = 2 A; $I_B$ = 200 mA; pulsed;<br>$t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; $T_{amb}$ = 25 °C   | -   | 250  | 350  | mV   |
| R <sub>CEsat</sub> | collector-emitter saturation resistance | $\begin{split} I_C = 1 \text{ A}; \ I_B = 0.1 \text{ A}; \ \text{pulsed}; \ t_p \leq 300 \ \mu\text{s}; \\ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^\circ\text{C} \end{split}$      | -   | 130  | 180  | mΩ   |
| V <sub>BEsat</sub> | base-emitter saturation voltage         | $\begin{split} I_{C} &= 500 \text{ mA; } I_{B} = 50 \text{ mA; pulsed;} \\ t_{p} &\leq 300  \mu\text{s; } \delta \leq 0.02 \text{ ; } T_{amb} = 25 ^{\circ}\text{C} \end{split}$  | -   | 0.88 | 1    | V    |
|                    |   | $I_{C}$ = 1 A; $I_{B}$ = 50 mA; pulsed;<br>$t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C  | -   | 0.91 | 1.05 | V    |
|                    |   | $I_C$ = 2 A; $I_B$ = 100 mA; pulsed;<br>$t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; $T_{amb}$ = 25 °C   | -   | 1    | 1.15 | V    |
|                    |   | $I_C$ = 2 A; $I_B$ = 200 mA; pulsed;<br>$t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; $T_{amb}$ = 25 °C   | -   | 1.05 | 1.2  | V    |
| V <sub>BEon</sub>  | base-emitter turn-on voltage            | $\label{eq:Vce} \begin{array}{l} V_{CE} = 2 \; V; \; I_{C} = 0.5 \; A; \; pulsed; \\ t_{p} \leq 300 \; \mu s; \; \delta \leq 0.02 \; ; \; T_{amb} = 25 \; ^{\circ} C \end{array}$ | -   | 0.77 | 0.9  | V    |
| t <sub>d</sub>     | delay time                              | $V_{CC}$ = 10 V; I <sub>C</sub> = 0.5 A; I <sub>Bon</sub> = 25 mA;  | -   | 15   | -    | ns   |
| t <sub>r</sub>     | rise time                               | I <sub>Boff</sub> = -25 mA; T <sub>amb</sub> = 25 °C  | -   | 85   | -    | ns   |
| t <sub>on</sub>    | turn-on time                            |   | -   | 100  | -    | ns   |
| t <sub>s</sub>     | storage time                            |   | -   | 545  | -    | ns   |
| t <sub>f</sub>     | fall time                               |   | -   | 125  | -    | ns   |
| t <sub>off</sub>   | turn-off time                           |   | -   | 670  | -    | ns   |
| f <sub>T</sub>     | transition frequency                    | $V_{CE}$ = 10 V; I <sub>C</sub> = 50 mA; f = 100 MHz;<br>T <sub>amb</sub> = 25 °C   | 120 | 180  | -    | MHz  |
| C <sub>c</sub>     | collector capacitance                   | V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A;<br>f = 1 MHz; T <sub>amb</sub> = 25 °C  | -   | 4.7  | 6    | pF   |

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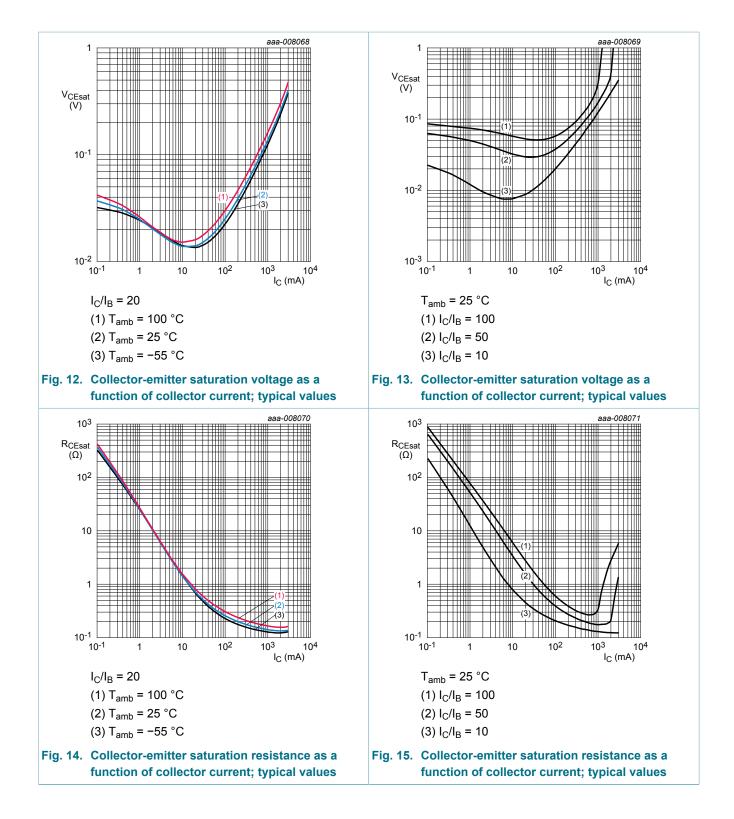


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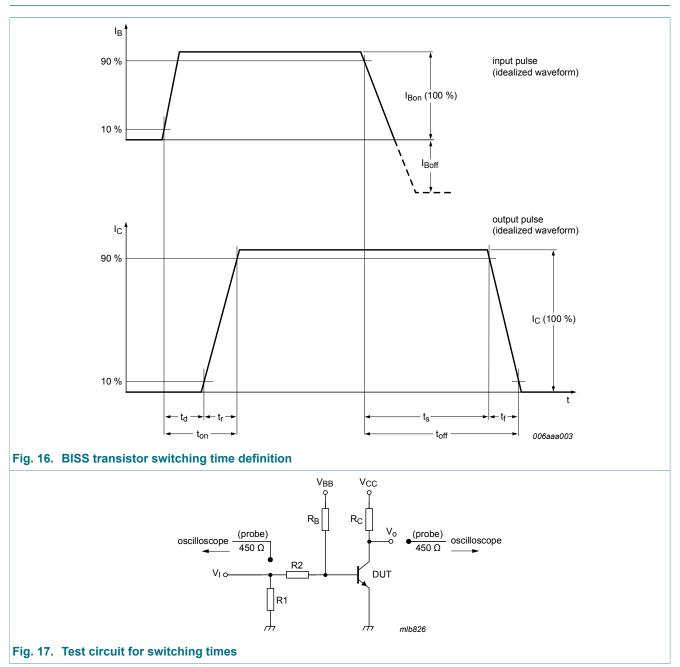


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### 11. Test information

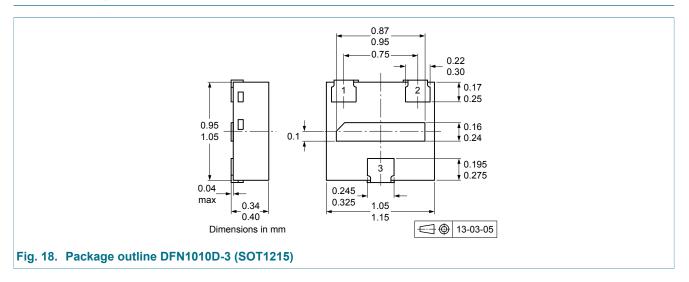
### **11.1 Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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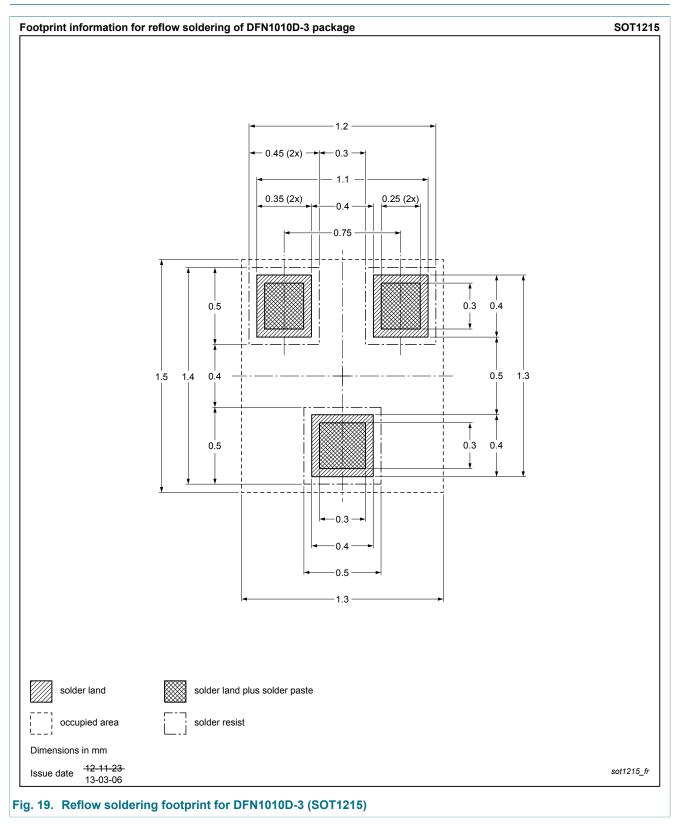
#### 60 V, 2 A NPN low VCEsat (BISS) transistor

# 12. Package outline



#### 60 V, 2 A NPN low VCEsat (BISS) transistor

### 13. Soldering



### 60 V, 2 A NPN low VCEsat (BISS) transistor

# 14. Revision history

| Table 8. Revision history |              |                    |               |            |  |  |
|---------------------------|--------------|--------------------|---------------|------------|--|--|
| Data sheet ID             | Release date | Data sheet status  | Change notice | Supersedes |  |  |
| PBSS4260QA v.1            | 20130828     | Product data sheet | -             | -          |  |  |

#### 60 V, 2 A NPN low VCEsat (BISS) transistor

### 15. Legal information

#### 15.1 Data sheet status

| Document status [1][2]               | Product<br>status [ <u>3]</u> | Definition  |
|--------------------------------------|-------------------------------|---|
| Objective<br>[short] data<br>sheet   | Development                   | This document contains data from<br>the objective specification for product<br>development. |
| Preliminary<br>[short] data<br>sheet | Qualification                 | This document contains data from the preliminary specification.                             |
| Product<br>[short] data<br>sheet     | Production                    | This document contains the product specification.   |

 Please consult the most recently issued document before initiating or completing a design.

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